

1. Scope

The present specifications shall apply to FMXA-1054S.

2. Outline

Type	Silicon Diode
Structure	Resin Molded Flammability:UL94-VO(Equivalent)
Applications	High Frequency Rectification, etc.

3. Absolute maximum ratings

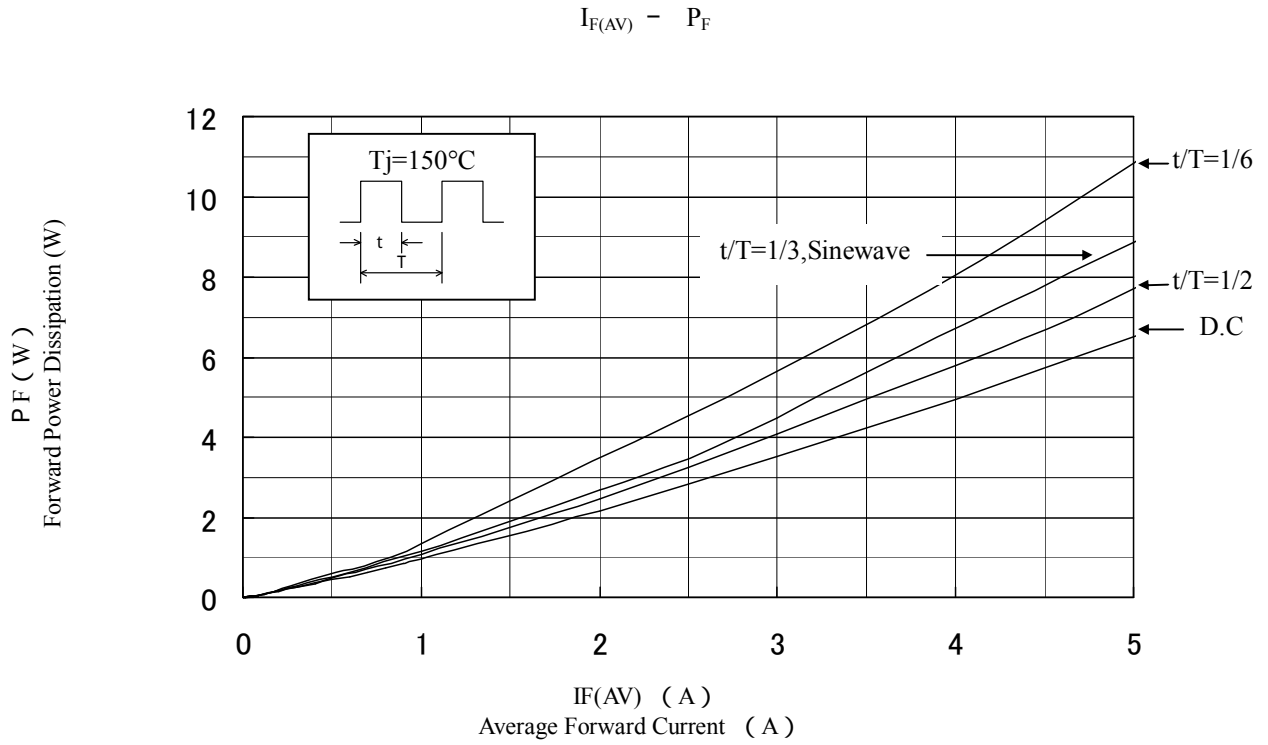
No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	VRSM	V	400	
2	Peak Reverse Voltage	VRM	V	400	
3	Average Forward Current	IF(AV)	A	5.0	Tc=108°C, sinewave
4	Peak Surge Forward Current	IFSM	A	50	10msec. 10msec. half sinewave, one shot
5	I ² t Limiting Value	I ² t	A ² S	12.5	
6	Junction Temperature	Tj	°C	-40~+150	
7	Storage Temperature	Tstg	°C	-40~+150	
8	Dielectric Strength		kV	A.C. 1 . 0	Junction and case(1minute)

4. Electrical characteristics (Ta=25°C, unless otherwise specified)

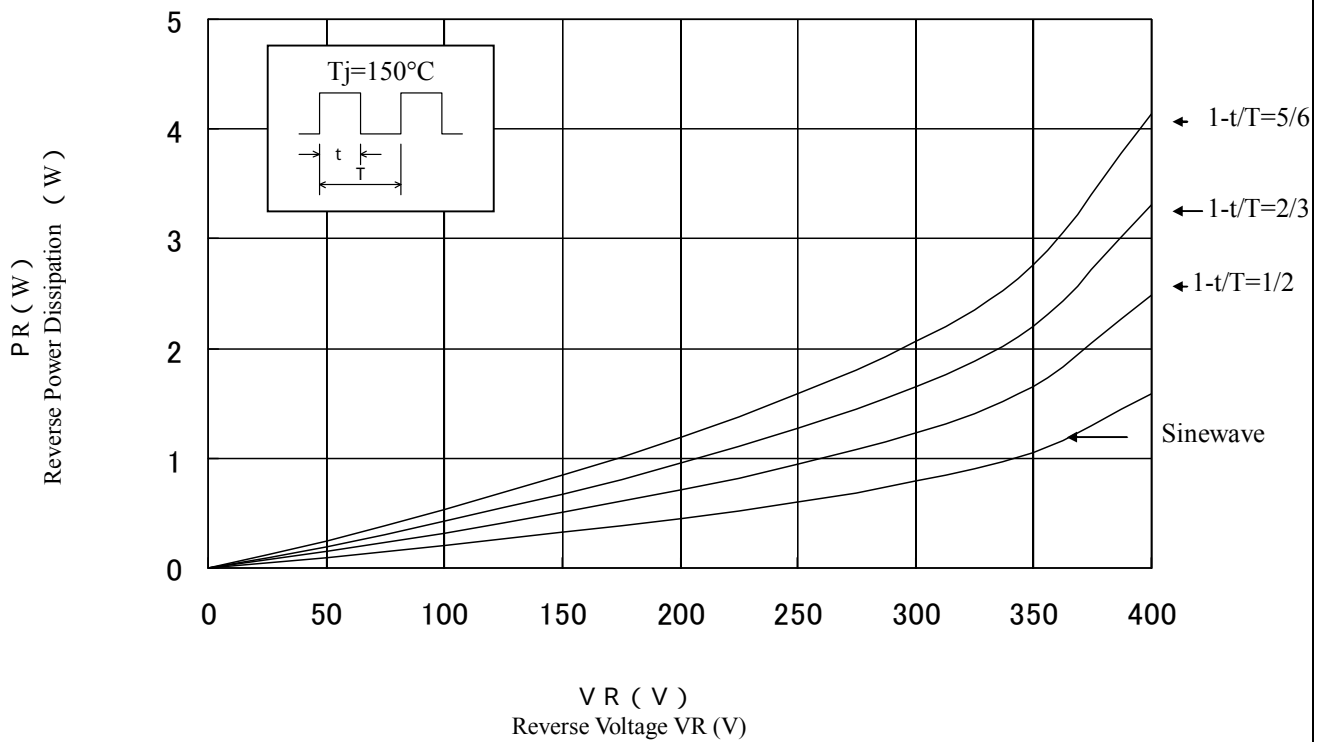
No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	VF	V	1.5 max.	IF=5 . 0A
2	Reverse Leakage Current	IR	uA	50 max.	VR=VRM
3	Reverse Leakage Current Under High Temperature	H• IR	mA	15 max.	VR=VRM , Tj=150□
4	Reverse Recovery Time	trr	ns	20 max.	IF = IRP = 500mA 90%Recovery point
5	Thermal Resistance	Rth(j-c)	°C /W	4.0 max.	Between Junction and case

4-1 Power Dissipation

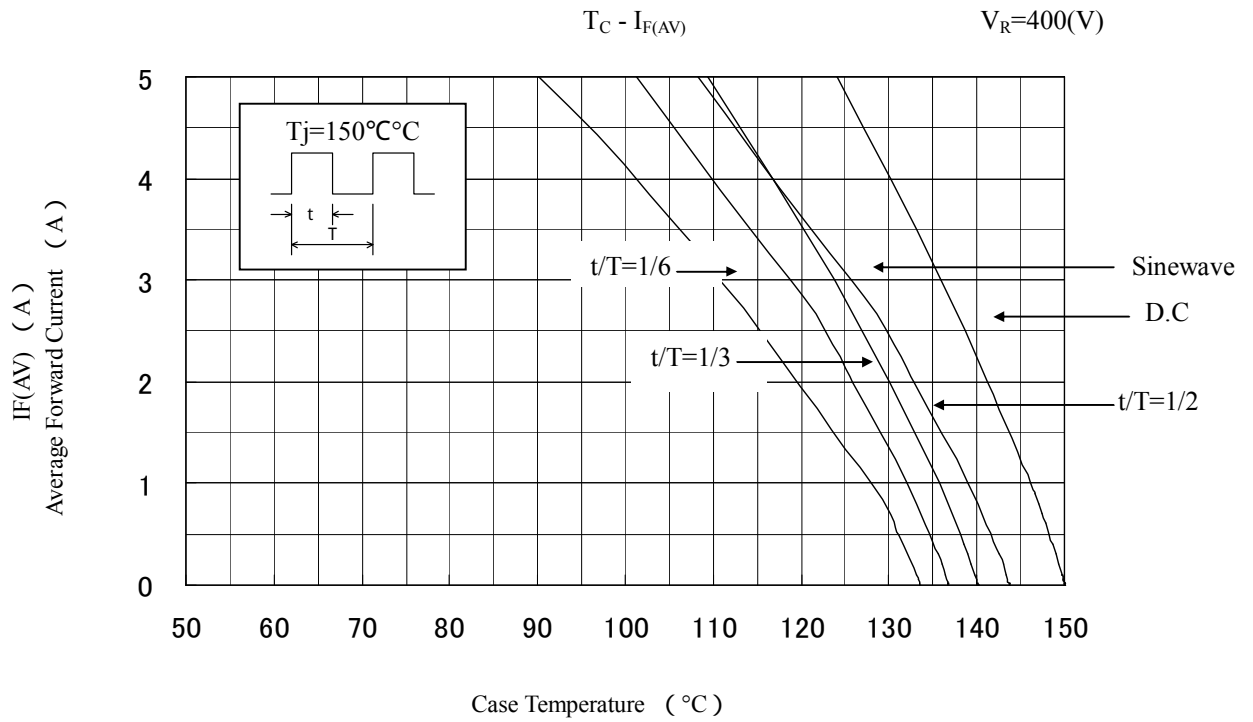
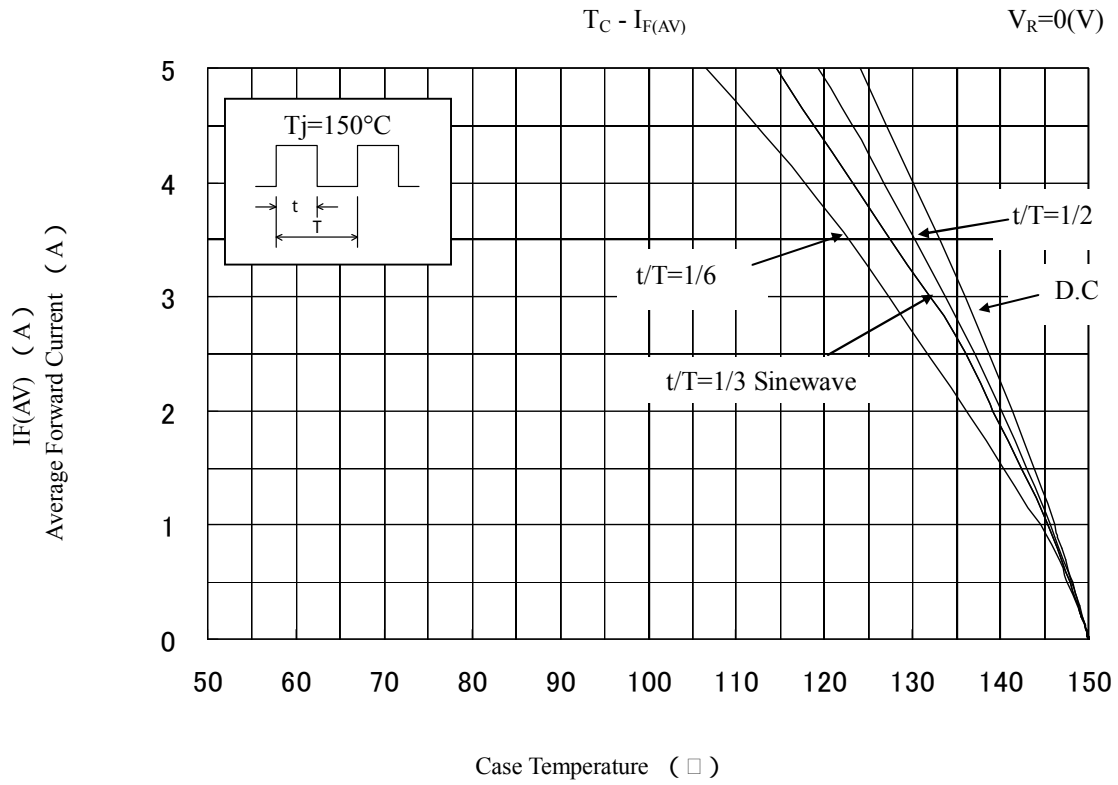
4-1-1 Average Forward Current—Forward Power Dissipation



4-1-2 Reverse Voltage—Reverse Power Dissipation

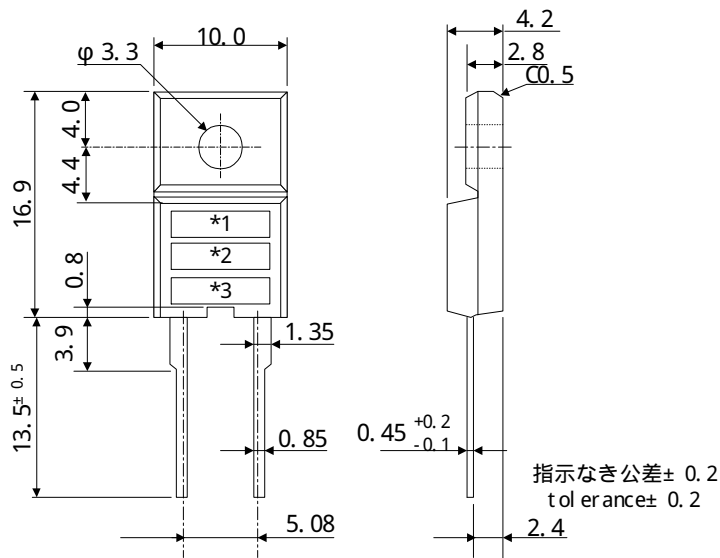


4-2 Derating Curve



5. Dimensions, Inner Structure and Marking

5-1 Dimensions Refer




Dimensions in mm

5-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

5-3 Marking

Type Name	Marking		
	*1 Type Name	*2 Polarity	*3 Lot number
FMXA-1054S	XA1054	S 	1st letter: Last digit of year 2nd letter: Month From 1 to 9 for Jan. to Sep., O for Oct., N for Nov., D for Dec. 3rd & 4th letter: Day ex. 3619 (Jun., 19, 2003)

5.